

ANGI095105-P52

X-Band matched GaN Device

Features:

Frequency: 9.5~10.5GHz

Saturated Output Power: $P_{sat} \geq 52\text{dBm}$

PowerGain: $\text{Gain} \geq 8.5\text{dB}$

Add-Efficiency: $\text{PAE} \geq 35\%$

Port Matching: $Z_{in}/Z_{out} = 50\Omega$

Description:

ANGI095105-P52 is an internal matching GaN device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 9.5~10.5GHz. This device can be used in different RF/Microwave system and subsystem.

The high output power level, high efficiency and wide operating temperature range can make application very flexible.

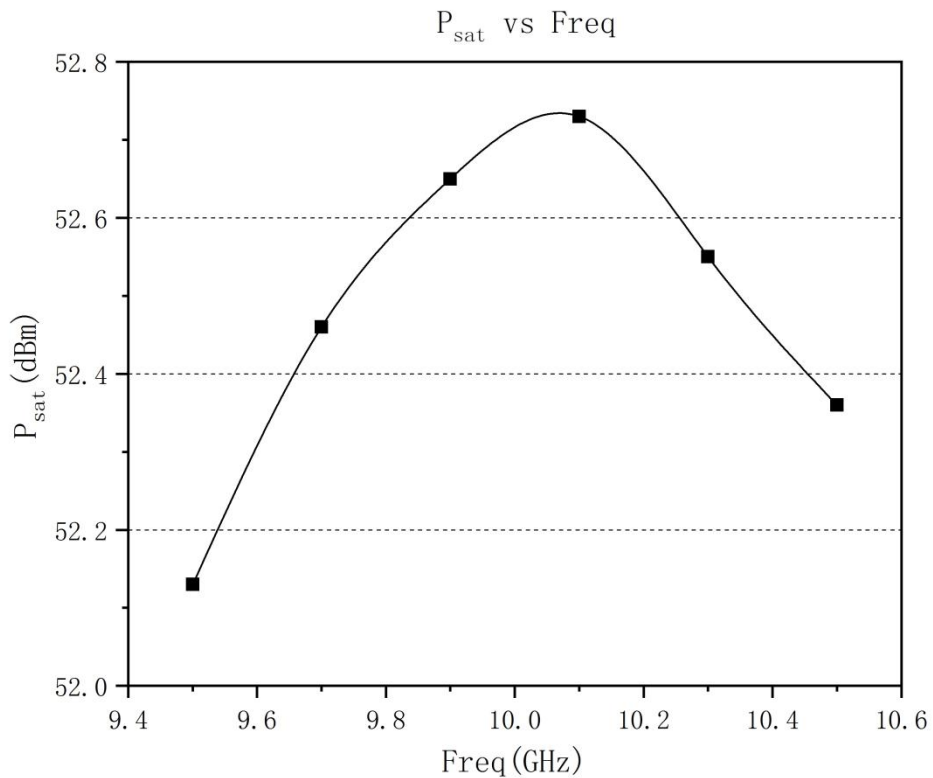
Maximun Ratings (TC=25°C, Not recommended working under this condition):

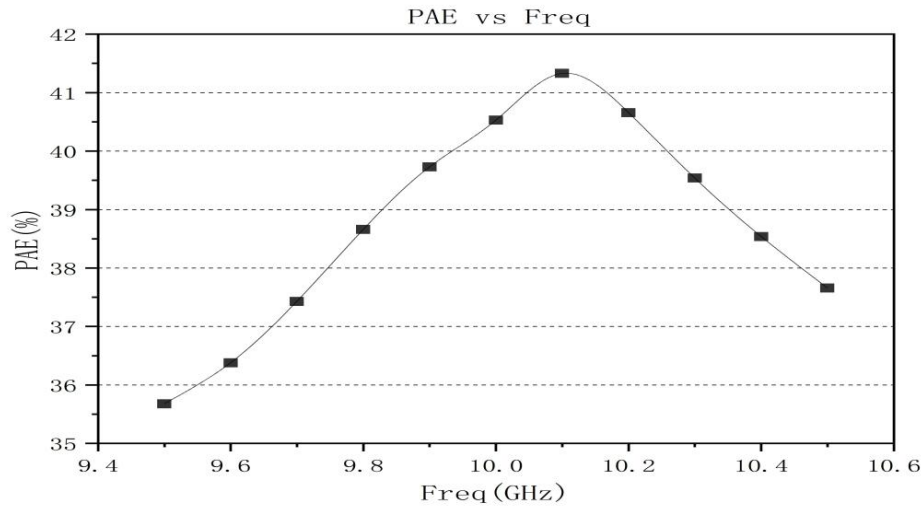
	Symbol	Value	Unit
Voltage between source and drain	V_{DS}	40	V
Voltage between gate and source	V_{GS}	-5	V
Storage Temperature Range	T_{stg}	-65 to +175	°C
Drain and Source Channel Temperature	T_{ch}	175	°C

Electrical Characteristics:

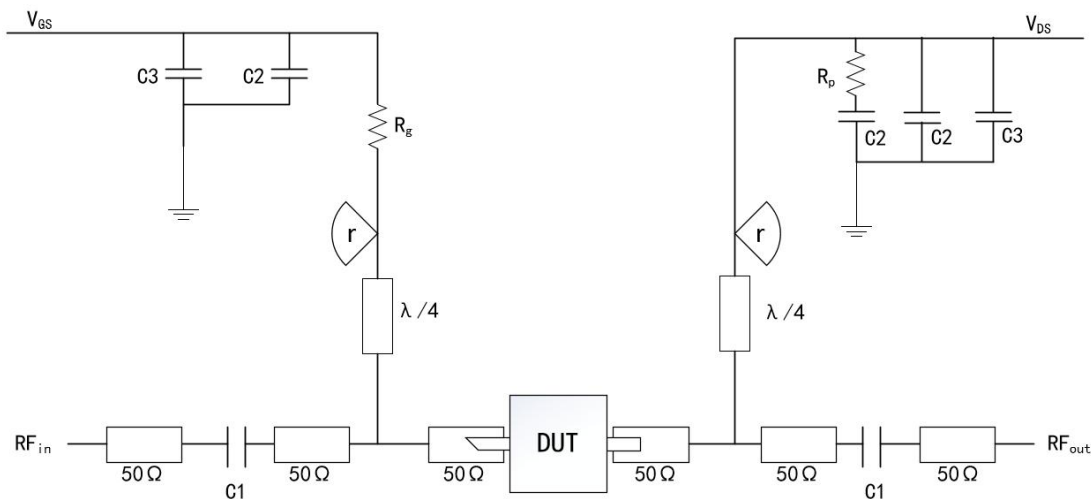
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I _{dsr}	V _{ds} =28V PW. T=1ms, Duty=10% Pin: 43.5dBm Freq: 9.5~10.5GHz	-	14	-	A
Saturated Output Power	P _{sat}		52	-	-	dBm
Gain	G _p		8.5	-	-	dB
Add-Efficiency	PAE		35	-	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





Application Circuit:



DUT: Device to be tested

C1:1pF

R_p :51Ω

C2:1000pF

R_g :15Ω

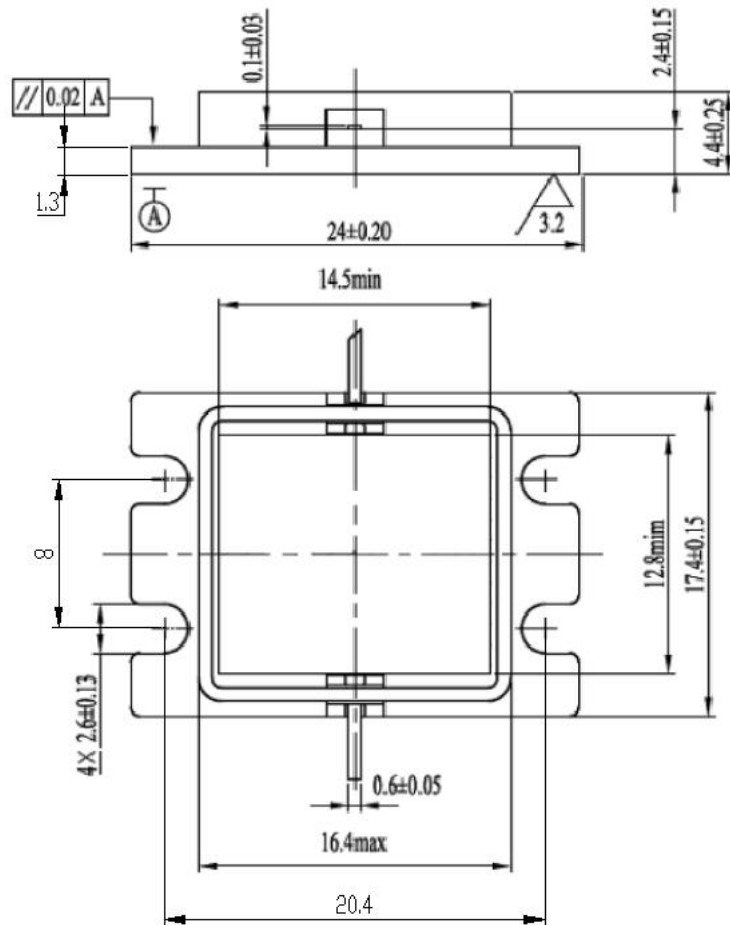
C3:100uF

r (radius) \approx 3.5mm(Rogers5880, 20mil)

ESD Level:

ESD	Class III	2000V
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Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.